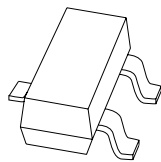


# DATA SHEET



**PBSS4140T**

40 V, 1A

NPN low  $V_{CEsat}$  (BISS) transistor

Product data sheet  
Supersedes data of 2005 Feb 14

2005 Feb 24

**40 V, 1A  
NPN low  $V_{CEsat}$  (BISS) transistor**

**PBSS4140T**

**FEATURES**

- Low collector-emitter saturation voltage
- High current capabilities.
- Improved device reliability due to reduced heat generation.

**APPLICATIONS**

- General purpose switching and muting
- LCD backlighting
- Supply line switching circuits
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

**DESCRIPTION**

NPN low  $V_{CEsat}$  transistor in a SOT23 plastic package.  
PNP complement: PBSS5140T.

**MARKING**

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
PBSS4140T	ZT*

**Note**

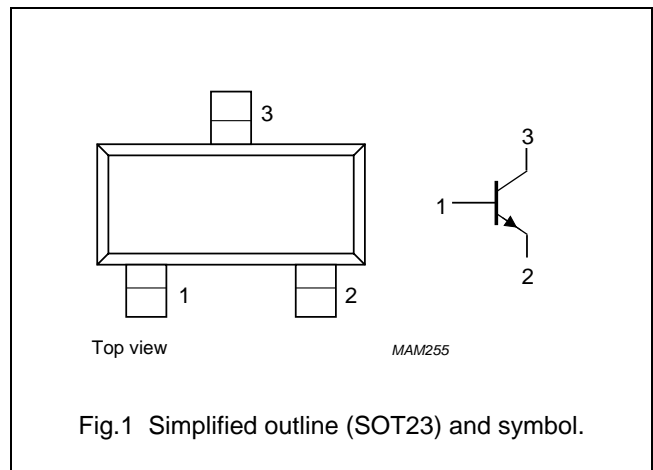
- \* = p: made in Hong Kong.  
\* = t: made in Malaysia.  
\* = W: made in China.

**QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	40	V
$I_{CM}$	peak collector current	2	A
$R_{CEsat}$	equivalent on-resistance	<500	mΩ

**PINNING**

PIN	DESCRIPTION
1	base
2	emitter
3	collector



**ORDERING INFORMATION**

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PBSS4140T	-	plastic surface mounted package; 3 leads	SOT23

40 V, 1A  
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PBSS4140T

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	40	V
$V_{CEO}$	collector-emitter voltage	open base	–	40	V
$V_{EBO}$	emitter-base voltage	open collector	–	5	V
$I_C$	collector current (DC)		–	1	A
$I_{CM}$	peak collector current		–	2	A
$I_{BM}$	peak base current		–	1	A
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 1	–	300	mW
		$T_{amb} \leq 25\text{ °C}$ ; note 2	–	450	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	operating ambient temperature		–65	+150	°C

**Notes**

1. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint.
2. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm<sup>2</sup>.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air; note 1	417	K/W
		in free air; note 2	278	K/W

**Notes**

1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.
2. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>.

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PBSS4140T

**CHARACTERISTICS** $T_{amb} = 25\text{ °C}$  unless otherwise specified.

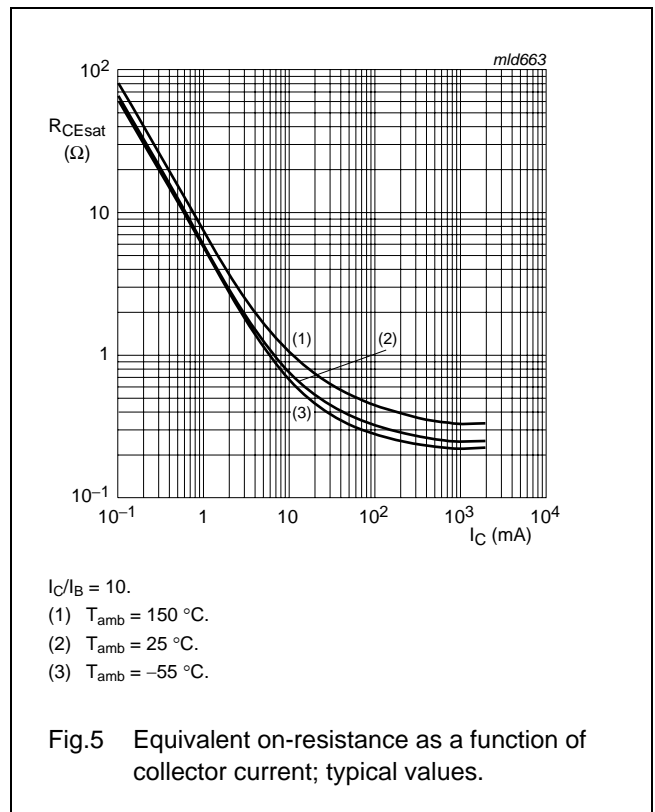
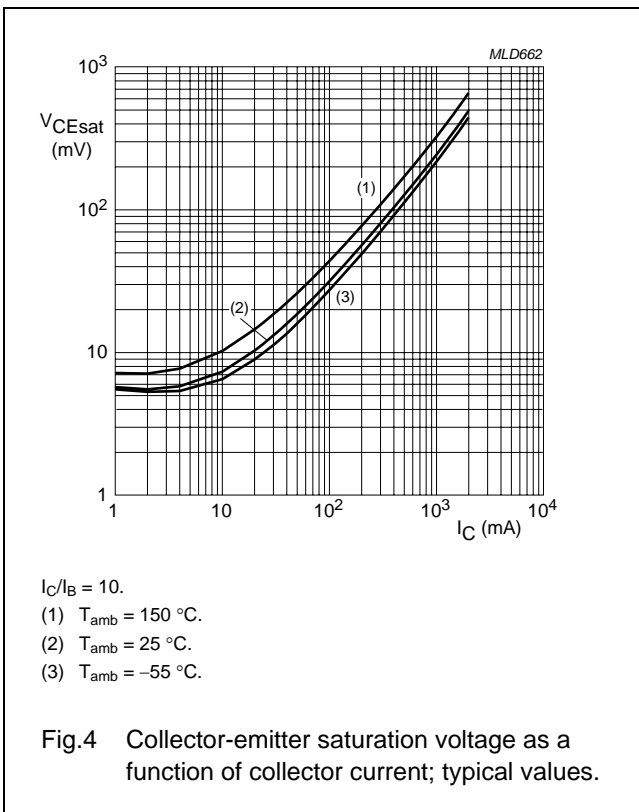
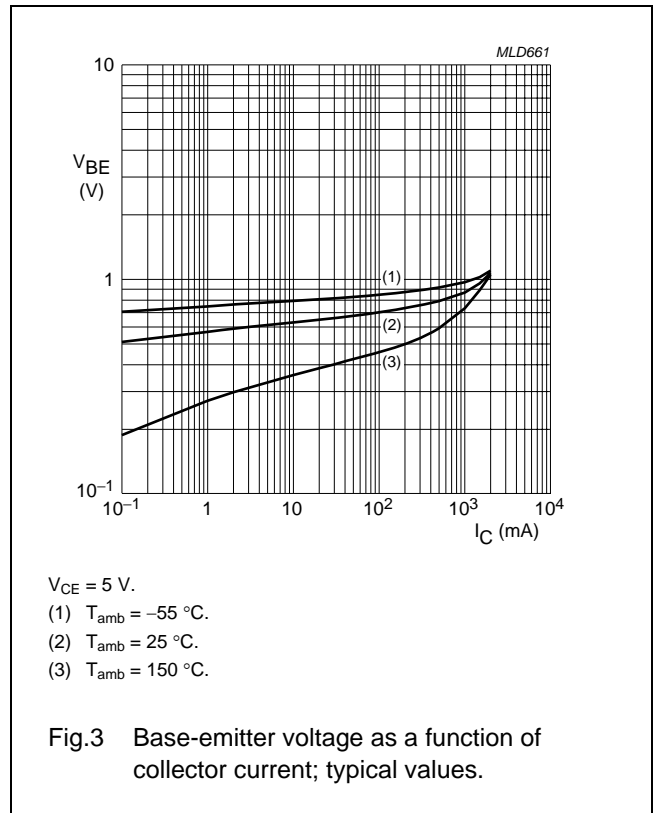
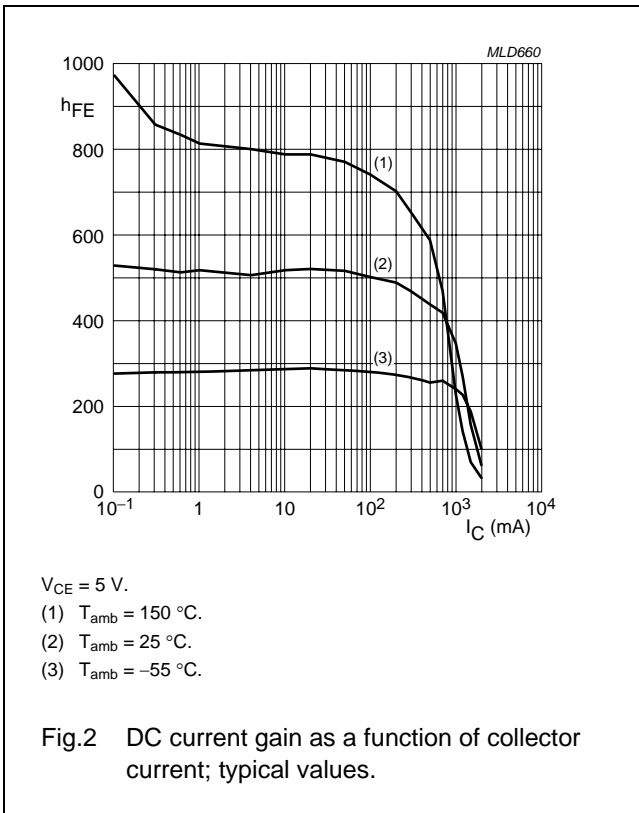
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 40\text{ V}; I_E = 0\text{ A}$	–	–	100	nA
		$V_{CB} = 40\text{ V}; I_E = 0\text{ A}; T_{amb} = 150\text{ °C}$	–	–	50	$\mu\text{A}$
$I_{CEO}$	collector-emitter cut-off current	$V_{CE} = 30\text{ V}; I_B = 0\text{ A}$	–	–	100	nA
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	–	–	100	nA
$h_{FE}$	DC current gain	$V_{CE} = 5\text{ V}; I_C = 1\text{ mA}$	300	–	–	
		$V_{CE} = 5\text{ V}; I_C = 500\text{ mA}$	300	–	900	
		$V_{CE} = 5\text{ V}; I_C = 1\text{ A}$	200	–	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 100\text{ mA}; I_B = 1\text{ mA}$	–	–	200	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	–	–	250	mV
		$I_C = 1\text{ A}; I_B = 100\text{ mA}$	–	–	500	mV
$R_{CEsat}$	equivalent on-resistance	$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	260	<500	$\text{m}\Omega$
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 100\text{ mA}$	–	–	1.2	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = 5\text{ V}; I_C = 1\text{ A}$	–	–	1.1	V
$f_T$	transition frequency	$I_C = 50\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	150	–	–	MHz
$C_c$	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_e = 0\text{ A}; f = 1\text{ MHz}$	–	–	10	pF

**Note**

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .

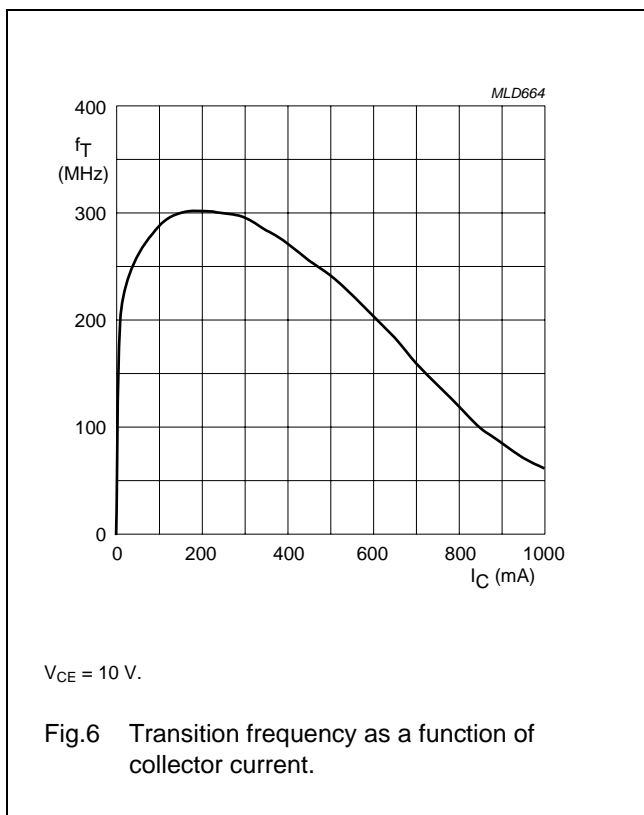
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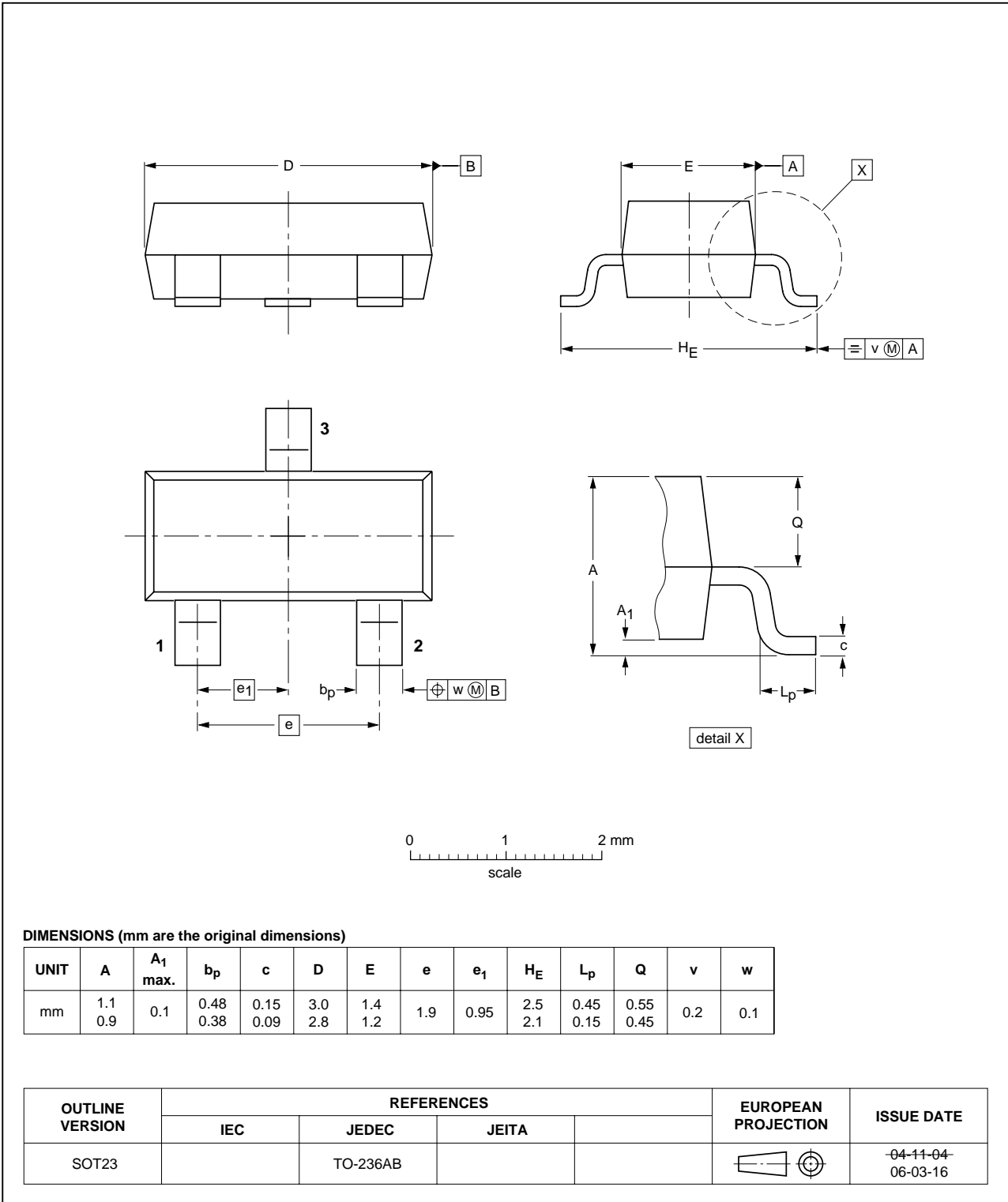
40 V, 1A  
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PBSS4140T

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



40 V, 1A  
NPN low  $V_{CEsat}$  (BISS) transistor

PBSS4140T

**DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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# ***NXP Semiconductors***

## **Customer notification**

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## **Contact information**

For additional information please visit: <http://www.nxp.com>

For sales offices addresses send e-mail to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

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